

# HiPerFET™ Power MOSFETs

Single MOSFET Die

N-Channel Enhancement Mode  
Avalanche Rated, High dv/dt, Low  $t_{rr}$

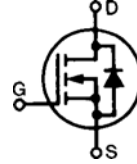
## IXFN 120N20

$$V_{DSS} = 200 \text{ V}$$

$$I_{D25} = 120 \text{ A}$$

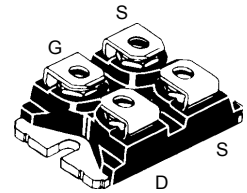
$$R_{DS(on)} = 17 \text{ m}\Omega$$

$$t_{rr} \leq 250 \text{ ns}$$



Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	200	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$	200	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	120	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	480	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	120	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	64	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	3	J
dv/dt	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$ , $R_G = 2 \Omega$	5	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	600	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.063 in.) from case for 10 s	-	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS $t = 1 \text{ min}$ $I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	2500 3000	V~ V~
$M_d$	Mounting torque Terminal connection torque	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
Weight		30	g

miniBLOC, SOT-227 B (IXFN)  
E153432



G = Gate                      D = Drain  
S = Source

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

### Features

- Encapsulating epoxy meets UL 94 V-0, flammability classification
- International standard package
- miniBLOC, with Aluminium nitride isolation
- Low  $R_{DS(on)}$  HDMOST™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

### Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls
- Low voltage relays

### Advantages

- Easy to mount
- Space savings
- High power density

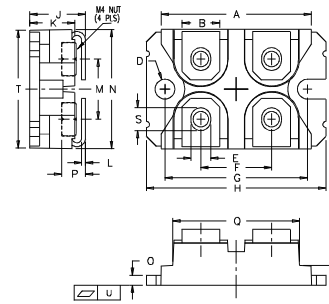
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 3 \text{ mA}$	200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8 \text{ mA}$	2		4 V
$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}$ , $V_{DS} = 0$			$\pm 200 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$		$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	100 $\mu\text{A}$ 2 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 \cdot I_{D25}$ Note 1			17 m $\Omega$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ Note 1	40	77	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		9100	pF
$C_{oss}$			2200	pF
$C_{rss}$			1000	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\ \Omega$ (External),		42	ns
$t_r$			55	ns
$t_{d(off)}$			110	ns
$t_f$			40	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		360	nC
$Q_{gs}$			50	nC
$Q_{gd}$			160	nC
$R_{thJC}$			0.22	K/W
$R_{thCK}$		0.05		K/W

Source-Drain Diode		Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$			120 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			480 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 50\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$			250 ns
$Q_{RM}$			1.1	$\mu\text{C}$
$I_{RM}$			13	A

Note: 1. Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle  $d \leq 2\%$

### miniBLOC, SOT-227 B

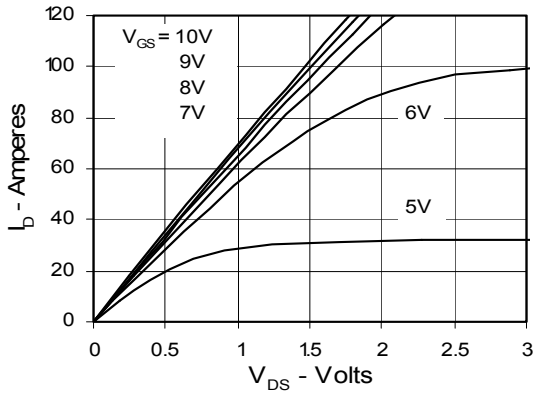
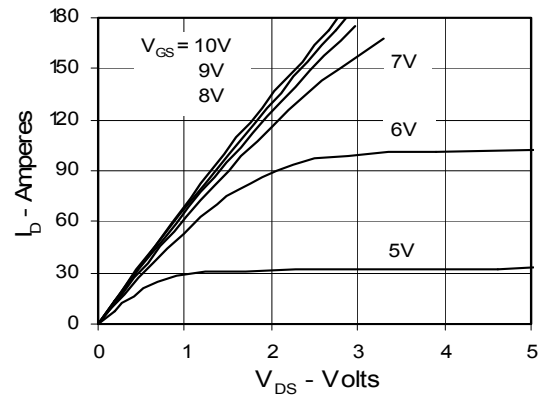
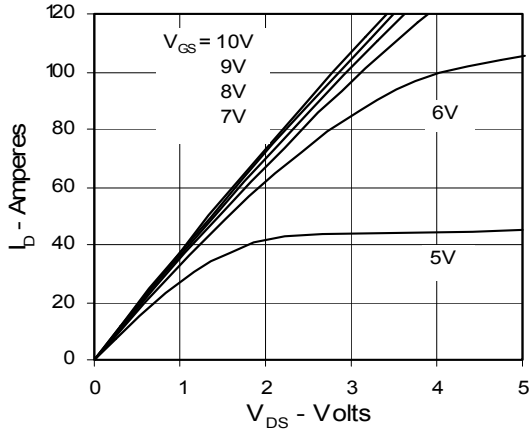
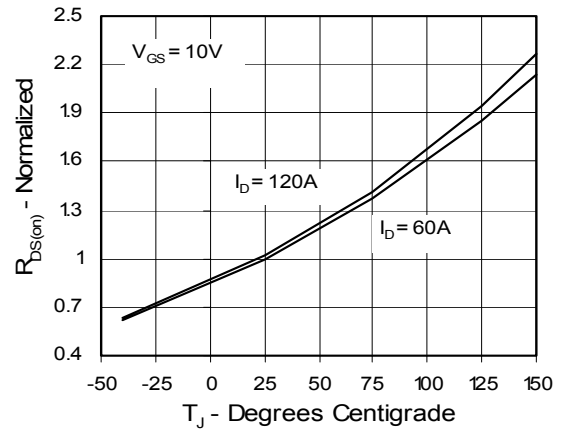
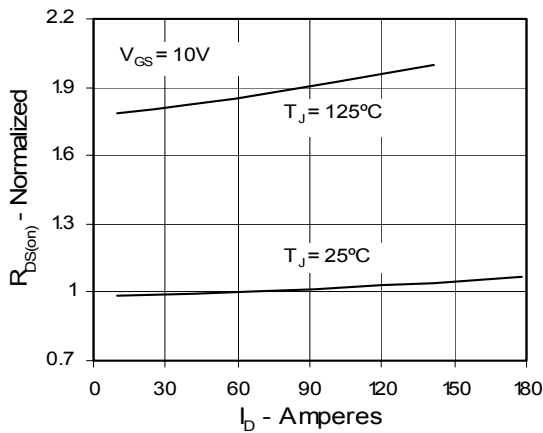
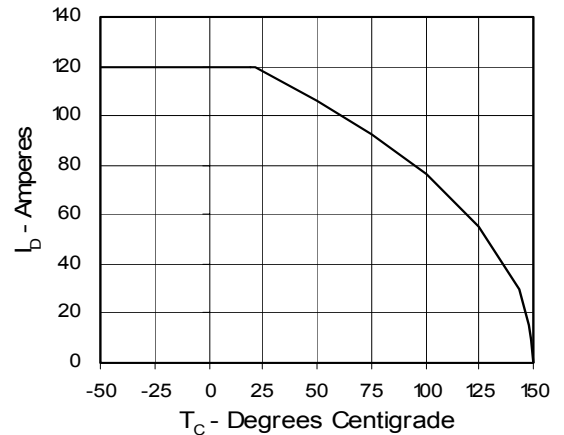


M4 screws (4x) supplied

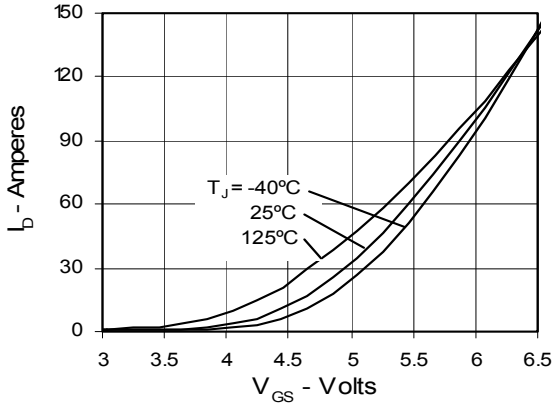
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

IXYS reserves the right to change limits, test conditions, and dimensions.

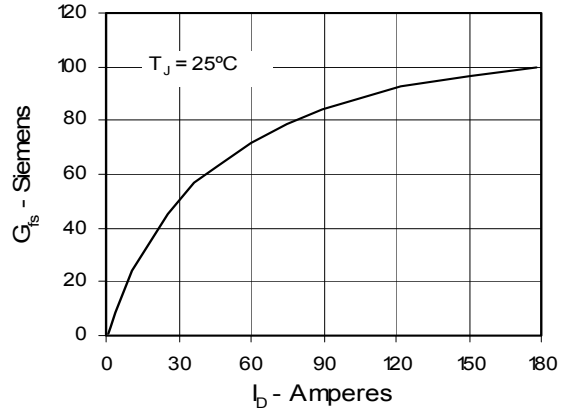
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

**Fig. 1. Output Characteristics  
@ 25 Deg. C**

**Fig. 2. Extended Output Characteristics  
@ 25 deg. C**

**Fig. 3. Output Characteristics  
@ 125 Deg. C**

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_{D25}$  Value vs.  
Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_{D25}$   
Value vs.  $I_D$** 

**Fig. 6. Drain Current vs. Case  
Temperature**


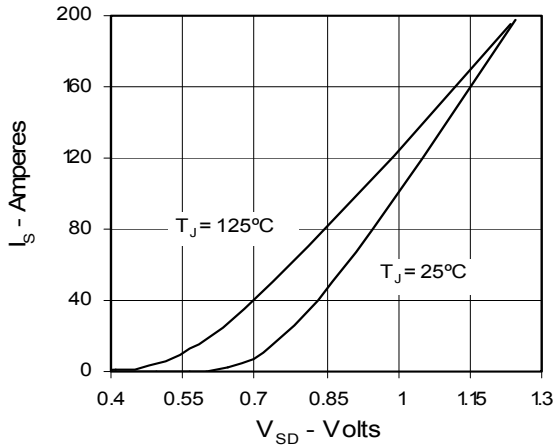
**Fig. 7. Input Admittance**



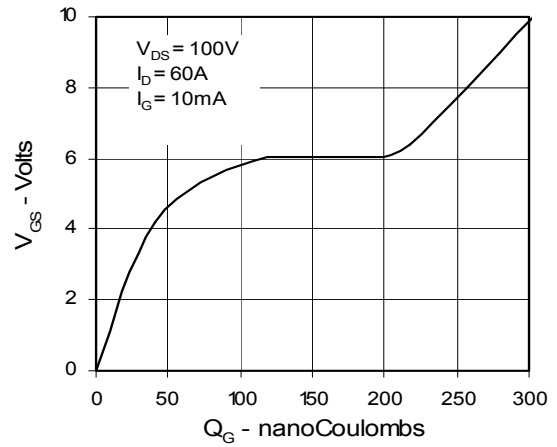
**Fig. 8. Transconductance**



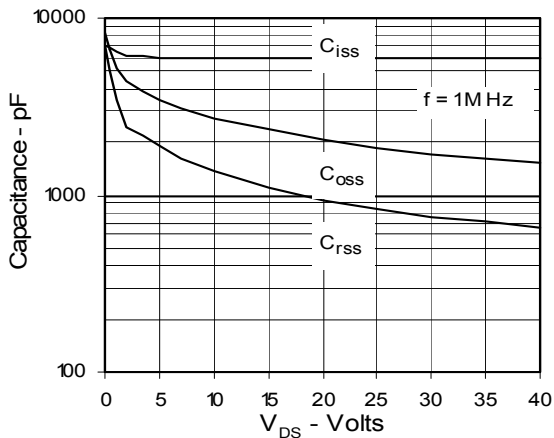
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



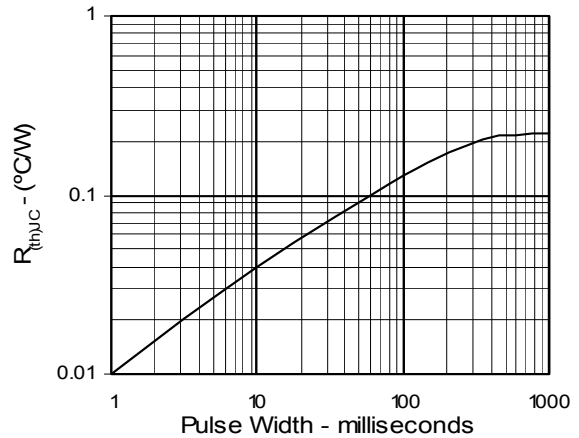
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Resistance**



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